

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☒ Surface-mounted package
- ☒ T_J 175°C
- ☒ Low $R_{DS(ON)}$ and Low gate charge
- ☒ MSL1

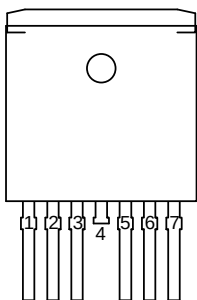
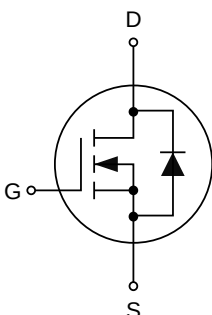
1.2 Applications

- ☒ BMS appliances
- ☒ Motor drives
- ☒ High power inverter system
- ☒ Light electric vehicles

1.3 Quick reference

- ☒ $BV \geq 100\text{ V}$
- ☒ $P_D \leq 395\text{ W}$
- ☒ $I_D \leq 370\text{ A}$
- ☒ $R_{DS(ON)} \leq 1.4\text{ m}\Omega @V_{GS} = 10\text{ V}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate(G)	 Top View TO-263-7L	
2, 3	Source(S)		
4	Drain(D)		
5, 6, 7	Source(S)		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}\text{C}$	100	-	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}\text{C}$	-	± 20	V
I_D^*	Drain Current (DC)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	370	A
		$T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	262	A
$I_{DM}^{*, **}$	Drain Current (Pulsed)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	1480	A
P_D	Power Dissipation	$T_C=25^{\circ}\text{C}$	-	430	W
I_S	Continuous-Source Current	$T_C=25^{\circ}\text{C}$	-	420	A
E_{AS}	Single Pulsed Avalanche Energy	$V_{DD}=50\text{ V}, L=0.3\text{ mH}$	-	2535	mJ
T_J, T_{stg}	Operating Junction and Storage Temperature Range		-55	175	$^{\circ}\text{C}$
$R_{\theta JA}^{**}$	Thermal Resistance-Junction to Ambient		-	56	$^{\circ}\text{C/W}$
$R_{\theta JC}^{**}$	Thermal Resistance-Junction to Case		-	0.38	$^{\circ}\text{C/W}$

Notes:

- * Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- ** Surface mounted on 1 in² pad area, $t \leq 10\text{ sec}$.
- *** Limited by bonding wire.

4. Marking Information

Product Name	Marking
KJ014N10D7	KJ014N10D7 HYWWXXX XXXXXX-X

5. Ordering Code

Product Name	Package	Reel size	Tape width	Quantity (pcs)
KJ014N10D7	TO-263-7L	13"	24 mm	800

Note: KUAJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C).

6. Electrical Characteristics (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _{DS} =250 μA	100	-	-	V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 μA	2	3	4	V
I _{DSS}	Drain Leakage Current	V _{DS} =80 V, V _{GS} =0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{DS} =0 V, V _{GS} =±20 V	-	-	±100	nA
R _{DS(ON)} ^a	On-State Resistance	V _{GS} =10 V, I _{DS} =20 A	-	1.2	1.4	mΩ
g _{fs}	Forward Transconductance	V _{DS} =5 V, I _{DS} =20 A	-	65	-	S
R _g	Gate Resistance	T _C =25°C	-	3.4	-	Ω
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	V _{GS} =0 V, I _{SD} =1 A	-	0.7	1.0	V
t _{rr}	Reverse Recovery Time	V _{DS} =50 V, V _{GS} =0 V, I _{DS} =20 A, di/dt=100 A/μs	-	110	-	ns
Q _{rr}	Reverse Recovery Charge		-	138	-	nC
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{DS} =50 V, V _{GS} =0 V, f=1 MHz	-	13680	-	pF
C _{oss}	Output Capacitance		-	2264	-	
C _{rss}	Reverse Transfer Capacitance		-	40	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =50 V, V _{GEN} =10 V, R _G =2.5 Ω, R _{GEN} =3 Ω	-	43	-	ns
t _r	Turn-on Rise Time		-	61	-	
t _{d(off)}	Turn-off Delay Time		-	135	-	
t _f	Turn-off Fall Time		-	76	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =50 V, V _{GS} =10 V, I _{DS} =20 A	-	130	-	nC
Q _{gs}	Gate-Source Charge		-	60	-	
Q _{gd}	Gate-Drain Charge		-	37	-	

Notes:

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

7. Typical Characteristics

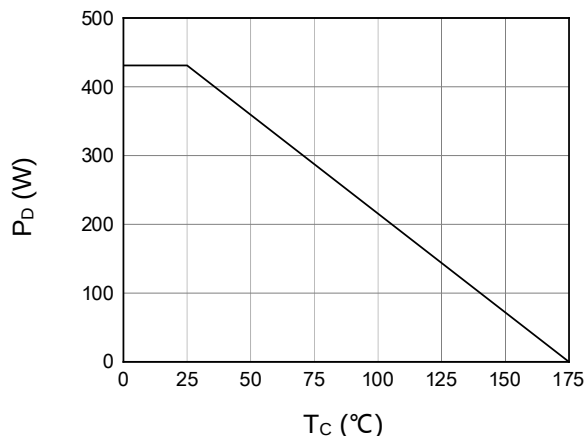


Figure 1. Power Capability

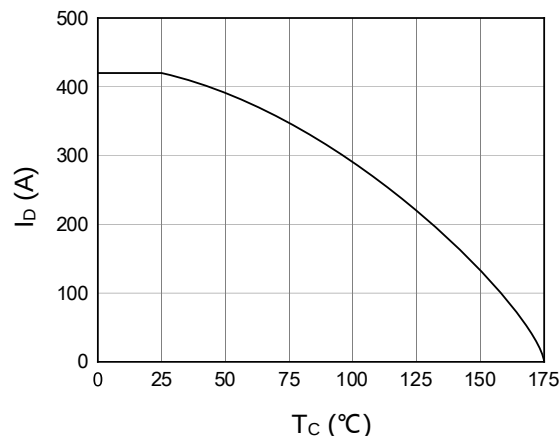


Figure 2. Current Capability

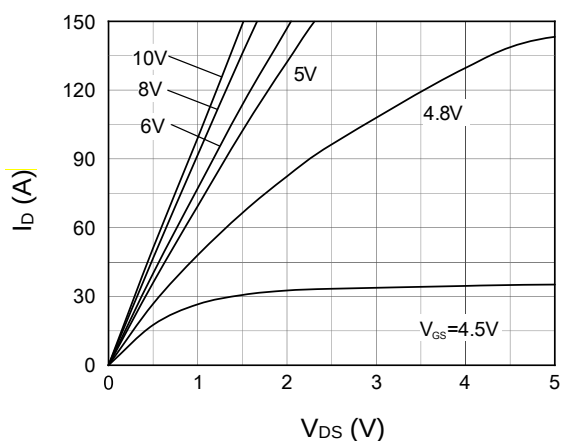


Figure 3. Output characteristics

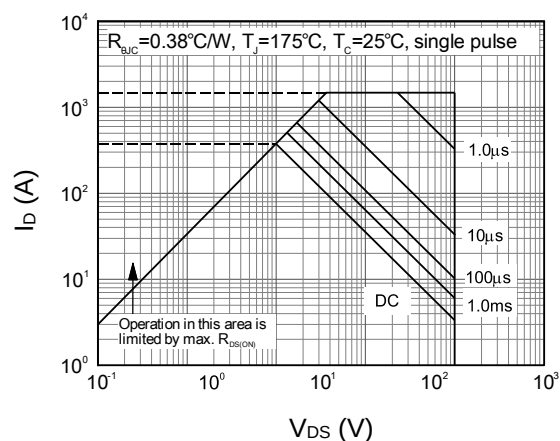


Figure 4. Safe operating area

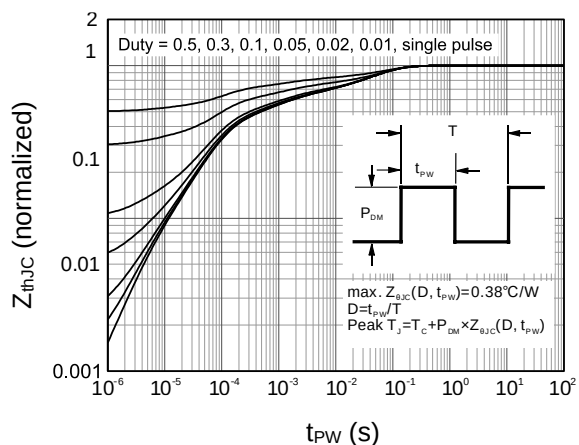


Figure 5. Normalized transient thermal impedance from junction to case

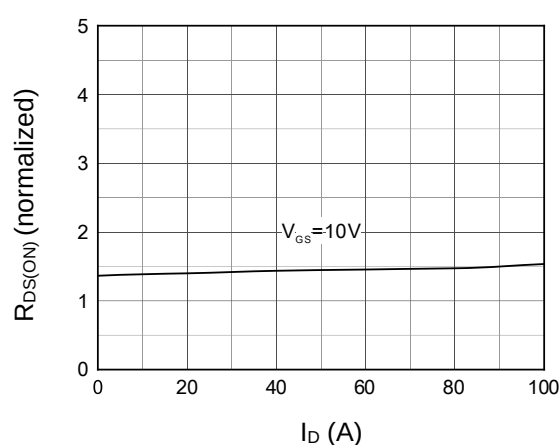


Figure 6. Normalized on-resistance vs drain current

7. Typical Characteristics (cont.)

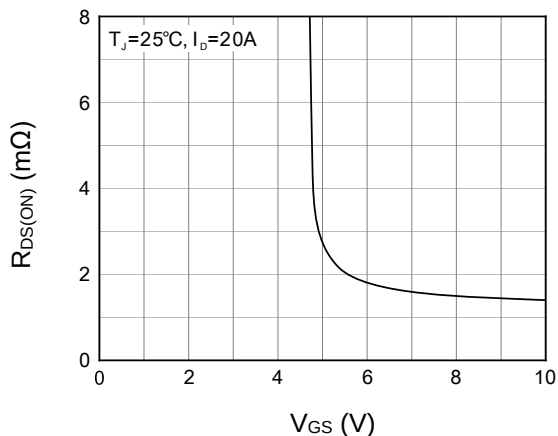


Figure 7. On-resistance vs gate-source voltage

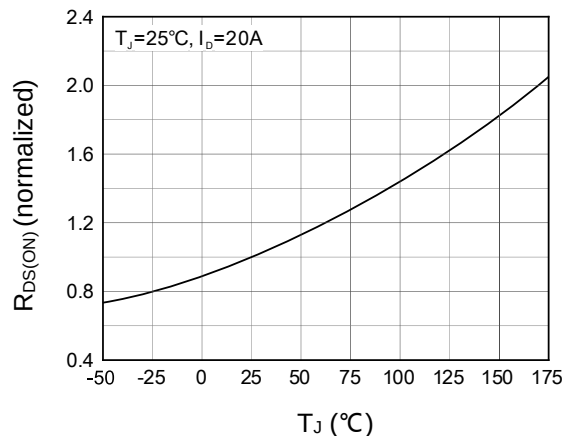


Figure 8. Normalized on-resistance vs junction temperature

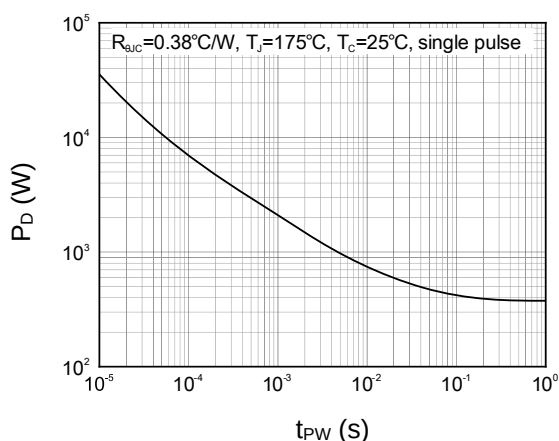


Figure 9. Single pulse maximum power dissipation

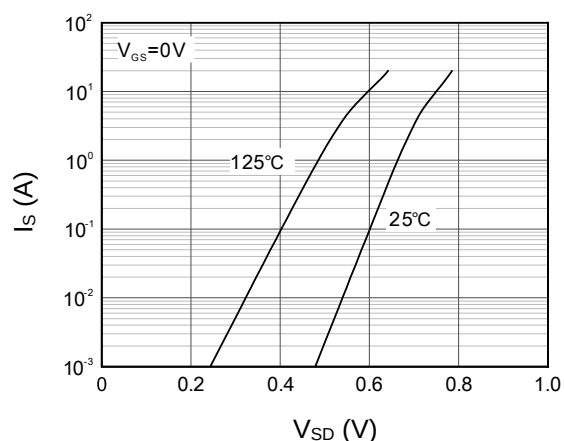


Figure 10. Forward characteristics of body diode

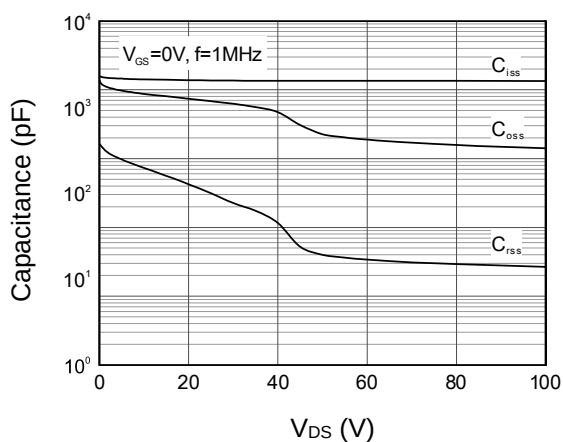


Figure 11. Capacitance

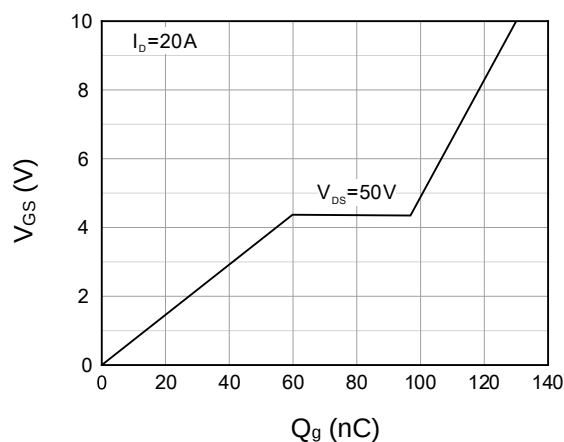
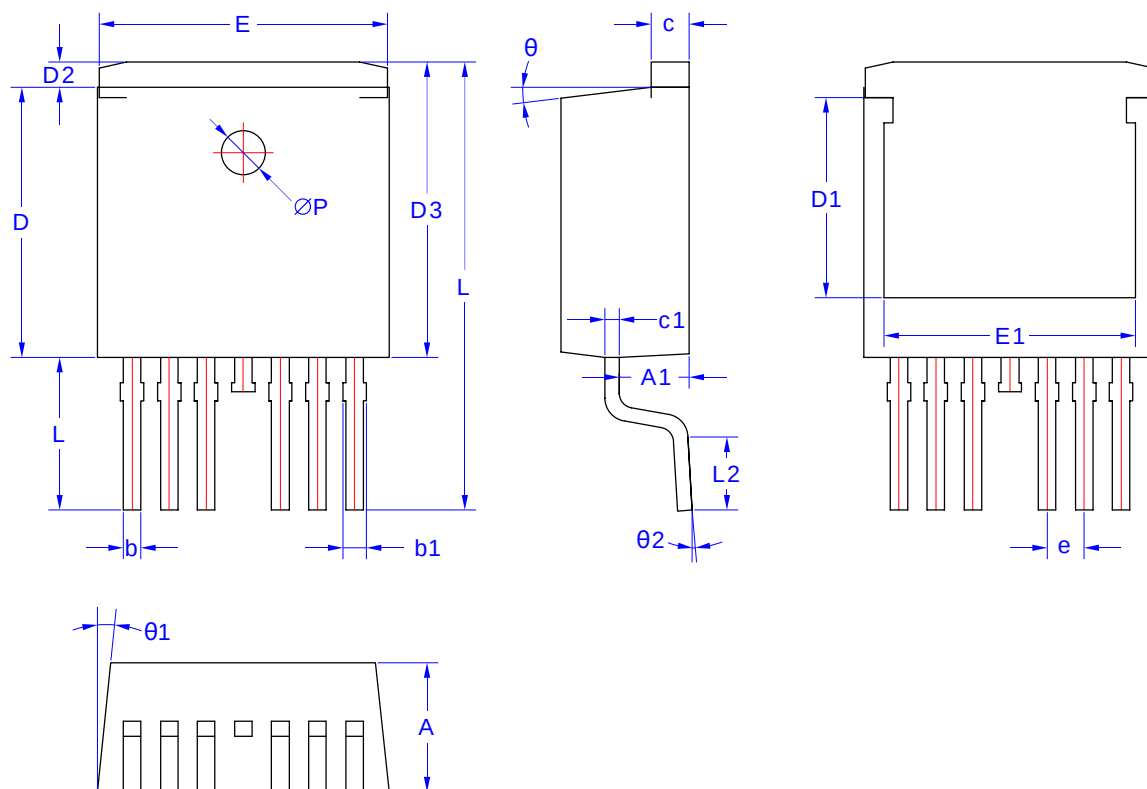


Figure 12. Gate charge

8. Package Dimensions

TO-263-7L Package



Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX
A	4.20	4.40	4.60
A1	2.30	2.40	2.50
b	0.50	0.60	0.70
b1	0.60	0.70	0.80
c	1.25	1.30	1.35
c1	0.45	0.50	0.55
D	9.05	9.25	9.45
D1	6.65	6.85	7.05
D2	0.65	0.85	1.05
D3	9.90	10.10	10.30

Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX
E	9.80	10.00	10.20
E1	8.50	8.60	8.70
e	-	1.27 BSC	-
L	14.90	15.10	15.40
L1	4.80	5.00	5.20
L2	2.30	2.50	2.70
θ	5°	7°	10°
$\theta1$	3°	5°	8°
$\theta2$	0°	-	8°
ΦP	-	1.50	-